

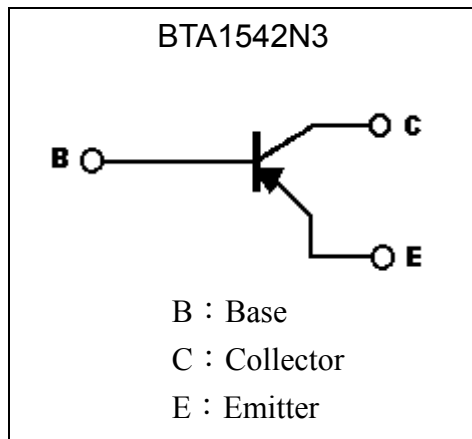
# PNP Epitaxial Planar Transistor

## BTA1542N3

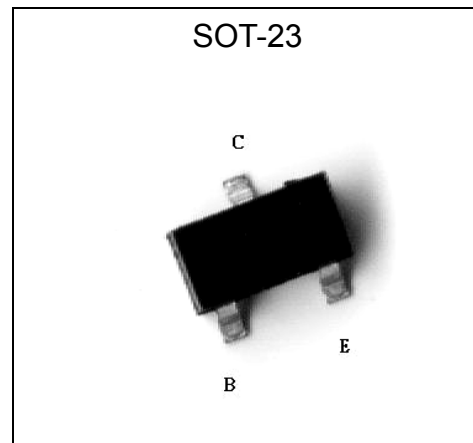
### Features

- Large current capability
- Low collector-to-emitter saturation voltage
- High speed switching
- Ultra small package facilitates miniaturization in end products
- High allowable power dissipation
- Pb-free lead plating and halogen-free package

### Symbol

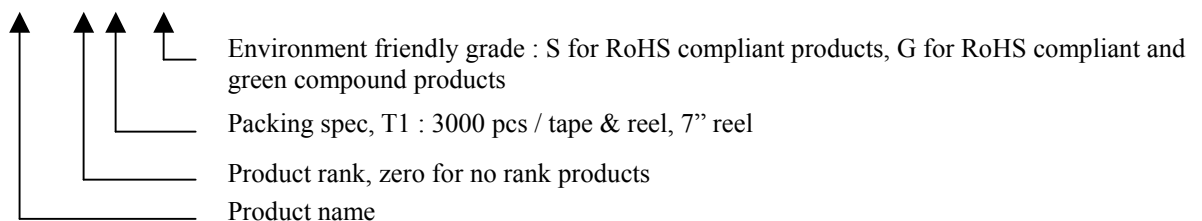


### Outline



### Ordering Information

Device	Package	Shipping
BTA1542N3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel





**Absolute Maximum Ratings** (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-Base Voltage		V <sub>CBO</sub>	-30	V
Collector-Emitter Voltage		V <sub>CEO</sub>	-20	V
Emitter-Base Voltage		V <sub>EBO</sub>	-5	V
Collector Current	DC	I <sub>C</sub>	-3	A
	Pulse	I <sub>CP</sub>	-5	
Base Current		I <sub>B</sub>	-600	mA
Power Dissipation		P <sub>d</sub>	225	mW
			0.9 (Note)	W
Junction Temperature		T <sub>j</sub>	150	°C
Storage Temperature		T <sub>stg</sub>	-55~+150	°C

Note : When device mounted on a ceramic board (600mm<sup>2</sup>×0.8mm)

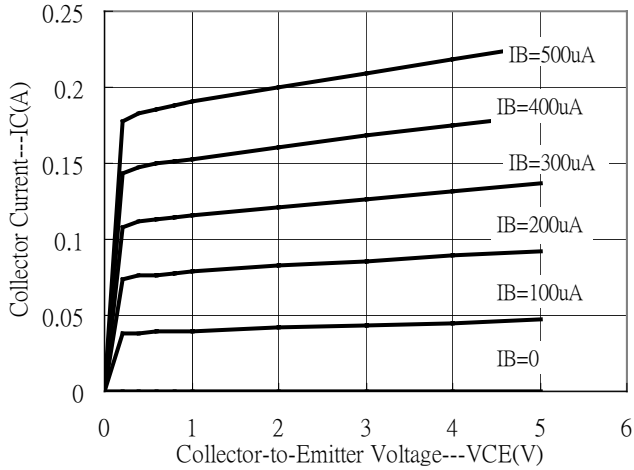
**Characteristics** (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	-30	-	-	V	I <sub>C</sub> =-10μA, I <sub>E</sub> =0
BV <sub>CEO</sub>	-20	-	-	V	I <sub>C</sub> =-1mA, I <sub>B</sub> =0
BV <sub>EBO</sub>	-5	-	-	V	I <sub>E</sub> =-10μA, I <sub>C</sub> =0
I <sub>CBO</sub>	-	-	-100	nA	V <sub>CB</sub> =-30V, I <sub>E</sub> =0
I <sub>EBO</sub>	-	-	-100	nA	V <sub>EB</sub> =-4V, I <sub>C</sub> =0
*V <sub>CE(sat)1</sub>	-	-	-300	mV	I <sub>C</sub> =-1.5A, I <sub>B</sub> =-30mA
*V <sub>CE(sat)1</sub>	-	-	-200	mV	I <sub>C</sub> =-1.5A, I <sub>B</sub> =-75mA
*V <sub>BE(sat)</sub>	-	-	-1.2	V	I <sub>C</sub> =-1.5A, I <sub>B</sub> =-30mA
*h <sub>FE</sub>	250	-	560	-	V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA
f <sub>T</sub>	-	380	-	MHz	V <sub>CE</sub> =-10V, I <sub>C</sub> =-500mA
C <sub>ob</sub>	-	25	-	pF	V <sub>CB</sub> =-10V, I <sub>E</sub> =0A, f=1MHz
ton	-	50	-	ns	V <sub>CC</sub> =-12V, R <sub>L</sub> =24Ω, I <sub>C</sub> =20I <sub>B1</sub> =-20I <sub>B2</sub> =-500mA
tstg	-	270	-	ns	
tf	-	25	-	ns	

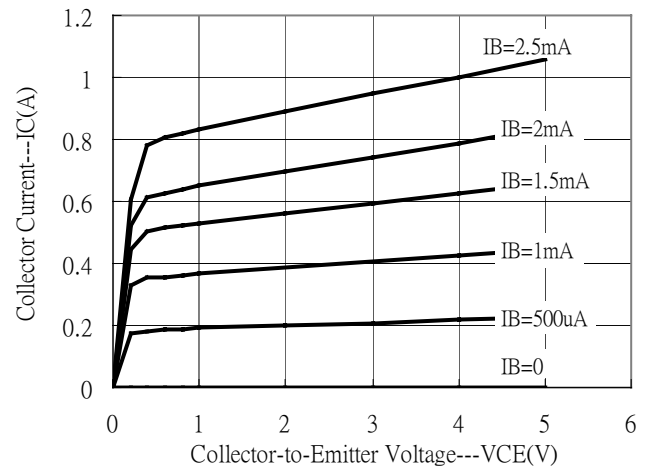
\*Pulse Test : Pulse Width ≤380μs, Duty Cycle ≤2%

**Typical Characteristics**

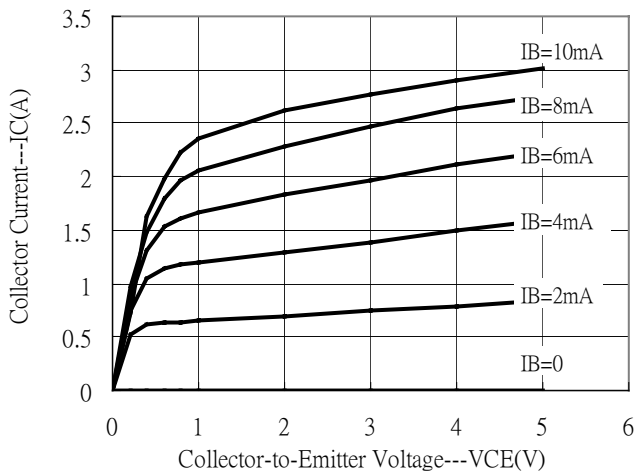
Output Characteristics



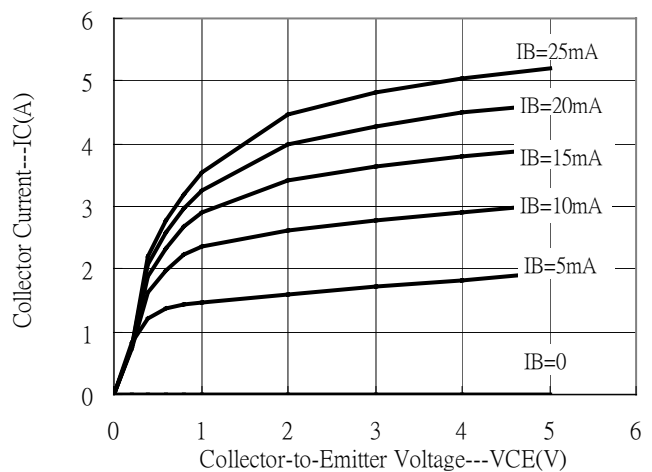
Output Characteristics



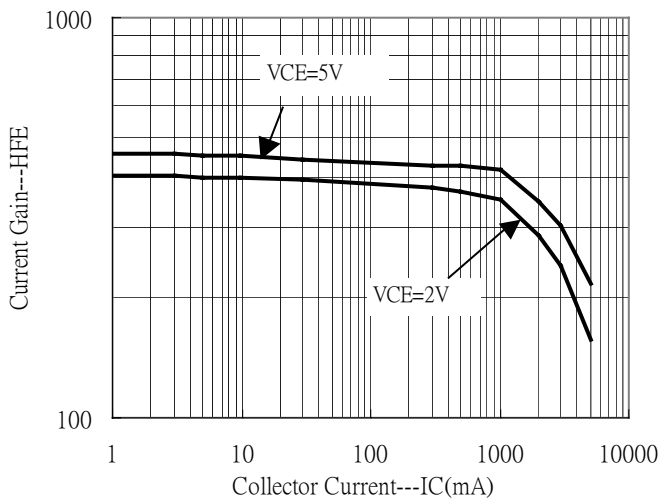
Output Characteristics



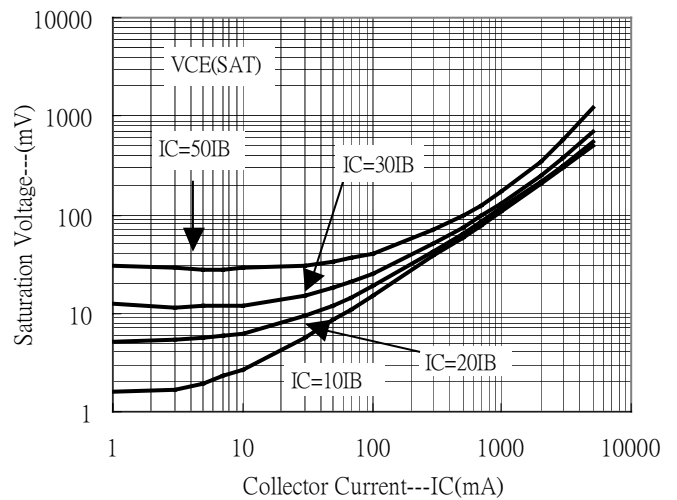
Output Characteristics



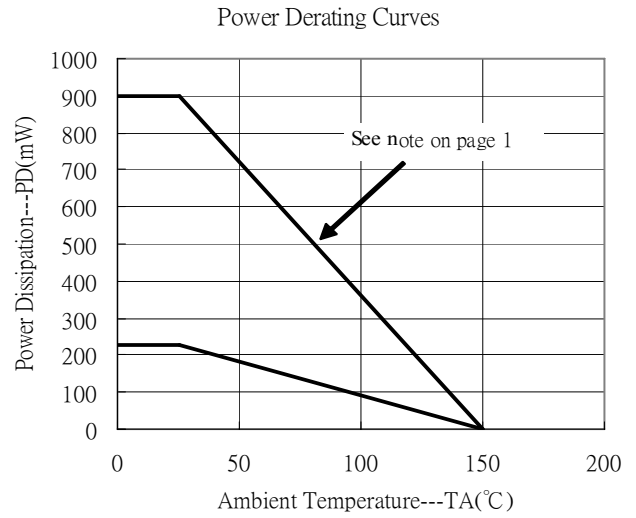
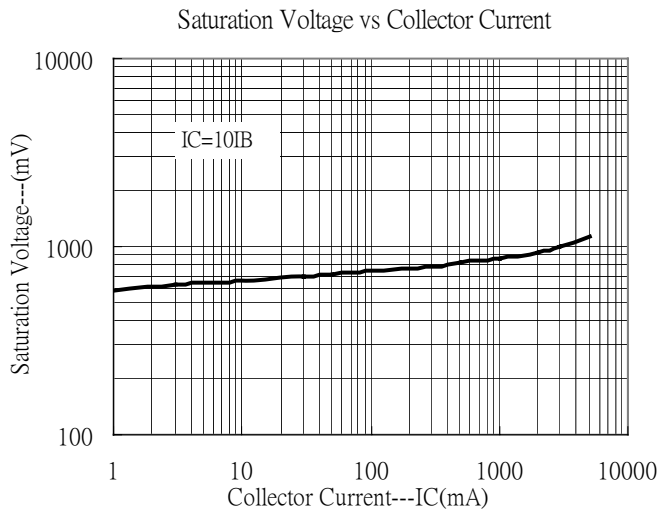
Current Gain vs Collector Current



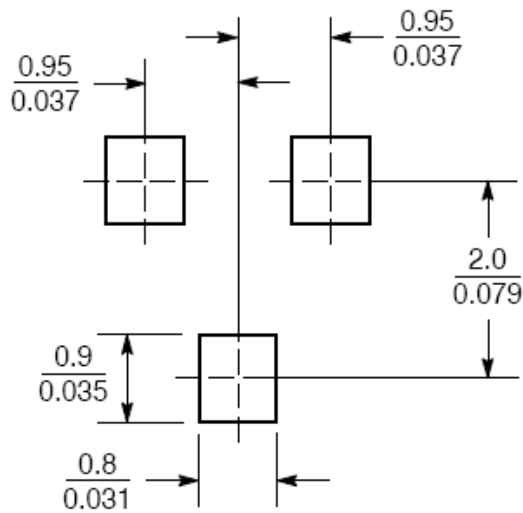
Saturation Voltage vs Collector Current



**Typical Characteristics(Cont.)**

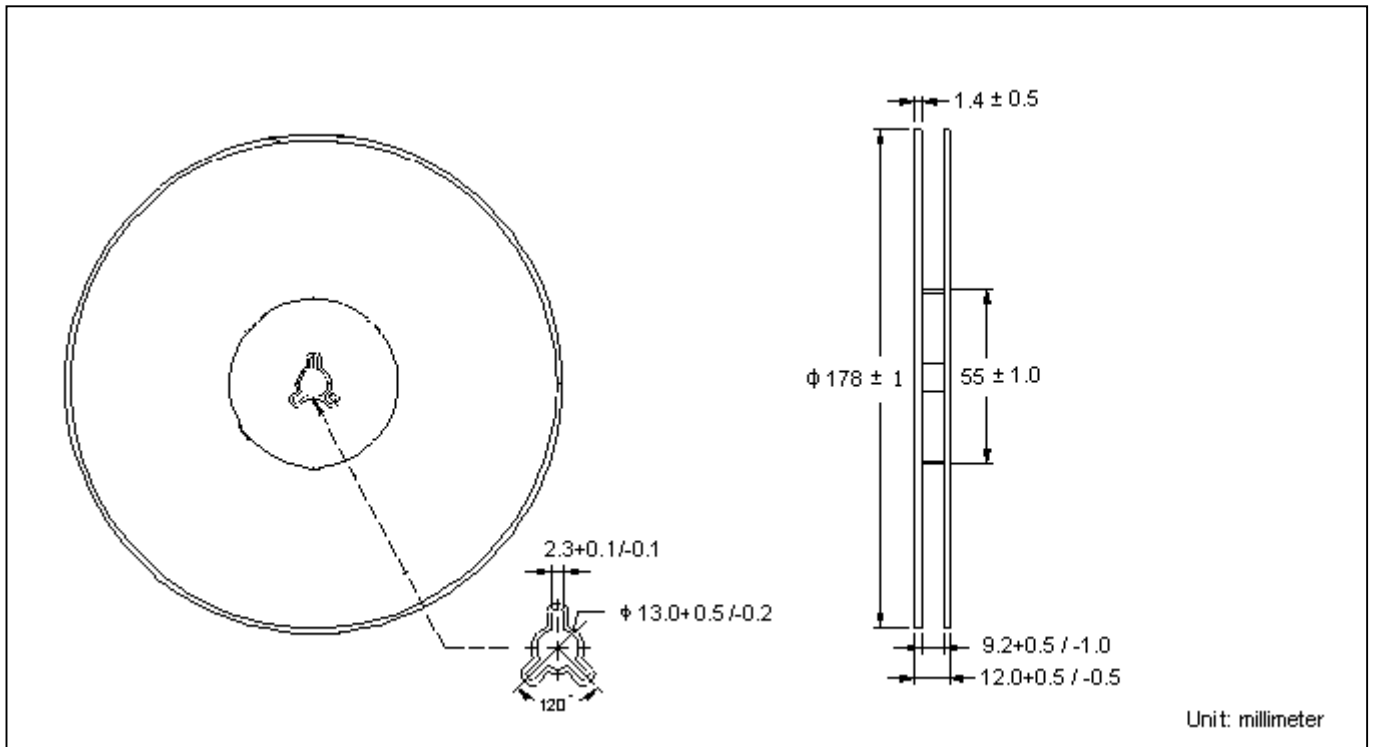


**Recommended Soldering Footprint**

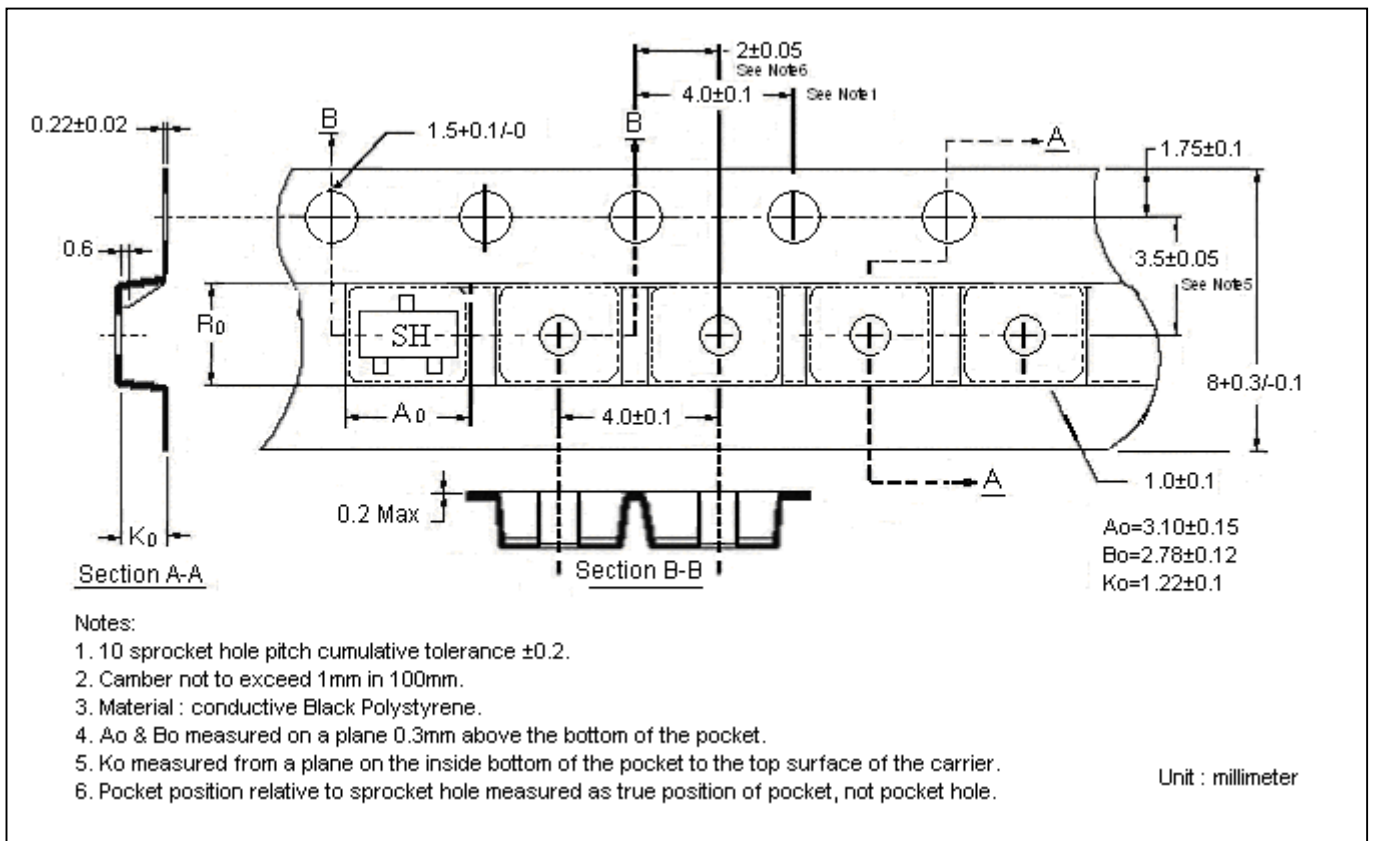


Unit :  $\frac{\text{mm}}{\text{inches}}$

**Reel Dimension**



**Carrier Tape Dimension**





**Product Designation**

BT X XXXX XX  
(1) (2) (3) (4)

(1) Indicates that transistor is bipolar

(2) Indicates polarity  
A, B . . . . PNP  
C, D . . . . NPN

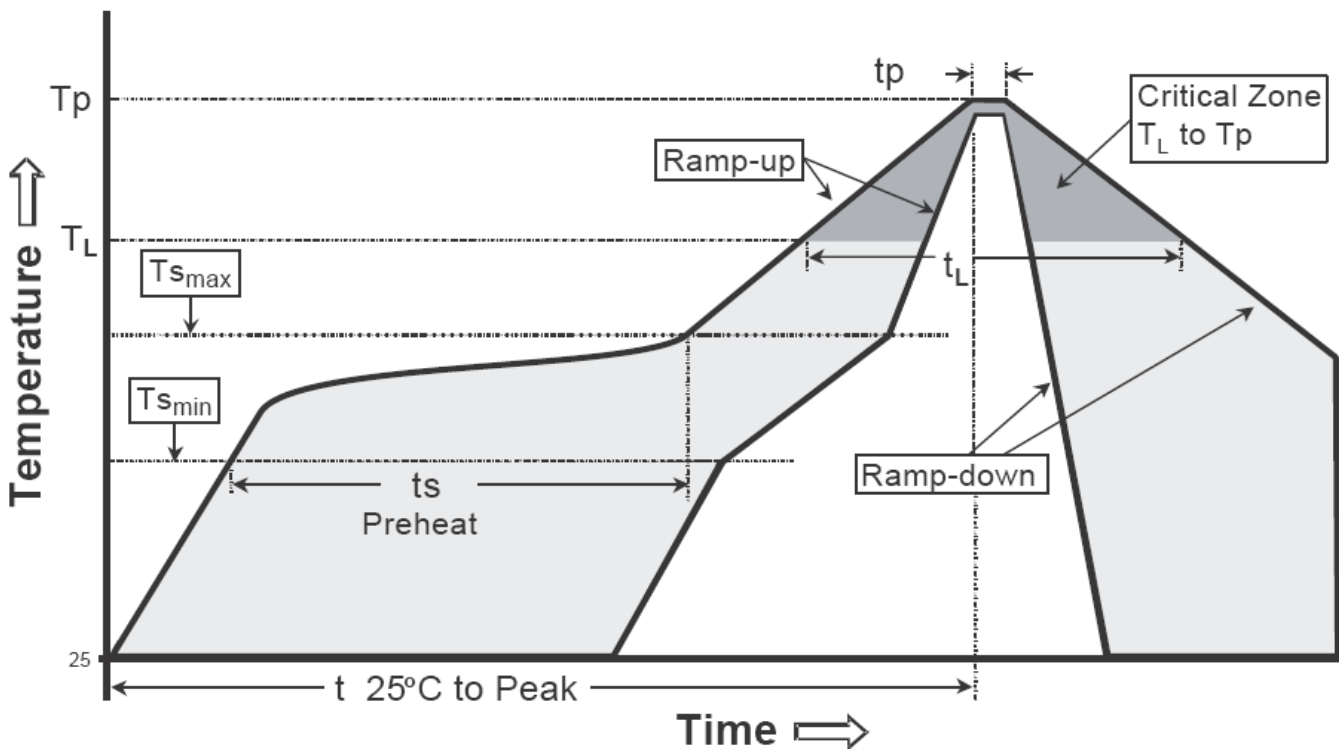
(3) Indicates device random number

(4) Indicates package shape  
N3 . . . SOT-23  
A3 . . . TO-92  
E3 . . . TO-220AB  
FP . . . TO-220FP  
J3 . . . TO-252  
I3 . . . TO-251  
F3 . . . TO-263  
D3 . . . TO-126ML  
T3 . . . TO-126  
L3 . . . SOT-223  
M3 . . . SOT-89  
S3 . . . SOT-323

**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

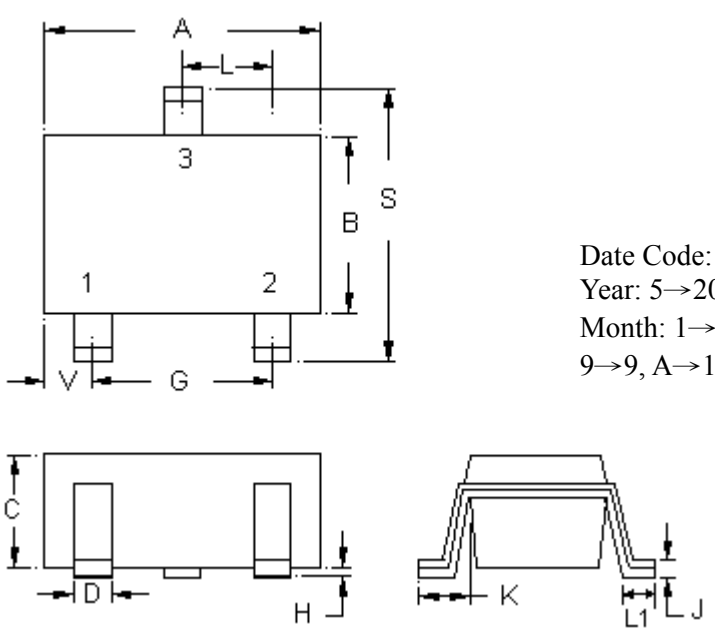
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> )	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T <sub>s min</sub> )	100°C	150°C
-Temperature Max(T <sub>s max</sub> )	150°C	200°C
-Time(t <sub>s min</sub> to t <sub>s max</sub> )	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>P</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(t <sub>p</sub> )	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

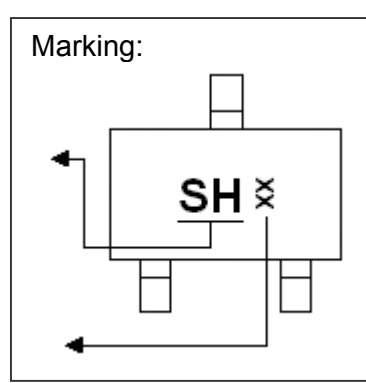
**SOT-23 Dimension**



Product Code

Date Code: Year+Month  
 Year: 5→2015, 6→2016  
 Month: 1→1, 2→2, . . .  
 9→9, A→10, B→11, C→12

Marking:



3-Lead SOT-23 Plastic Surface Mounted Package  
 CYStek Package Code: N3

Style : Pin 1.Base 2.Emitter 3.Collector

\*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0669	1.20	1.70	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10	L1	0.0118	0.0197	0.30	0.50

- Notes : 1.Controlling dimension : millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material :**

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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